

Form PTO-1449 (REV. 7-80) PATENT AND TRADEMARK OFFICE	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	Atty. Docket No. YOR920030334US1 (16899)	Serial No. 10/786,901
LIST OF REFERENCES CITED BY APPLICANT (Use several sheets if necessary)		Applicant: Ricky S. Amos et al.	
		Filing Date: February 25, 2004	Group/Art Unit: 2891

U.S. PATENT DOCUMENTS

EXAMINER INITIAL*	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (if appropriate)
AKS	4,780,429	10/25/1988	Roche et al.			
	5,986,313	11/16/1999	Ueda et al.			
	6,458,702	10/1/2002	Aloni			
	6,656,764	12/2/2003	Wang et al.			
	2002/123222	9/5/2002	Wu			
AKS	2003/230811	12/18/2003	Kim			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
AKS	2 804 793	8/10/2001	France				
	WO 99/53535	10/21/1999	PCT				
AKS	2002-217411	8/2/2002	Japan				

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

AKS	"Self-Aligned Technique Employing Planarized Resist For Reducing Poly-Silicon Sheet Resistance By Formation of a Metal Silicide." IBM Technical Disclosure Bulletin, IBM Corp. Vol. 30 No. 5 (1987)

EXAMINER: <i>Ashe Kumar Sathar</i>	DATE CONSIDERED: <i>11/30/06</i>
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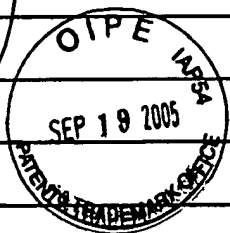
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INFORMATION DISCLOSURE CITATION
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Docket Number (Optional) YOR920030334US1 (16899)		Application Number 10/786,901
Applicant(s) Ricky S. Amos et al.		
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U.S. PATENT APPLICATION PUBLICATIONS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
AKS		2003/0141565 A1	7/31/2003	Hirose et al.			

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

AKS		Oh J. et al. "Interdigitated Ge p-i-n Photodetectors Fabricated on a Si Substrate Using Graded SiGe Buffer Layers." IEEE Journal of Quantum Electronics, vol. 38, no. 9, (2002)
AKS		Jones R.E. et al. "Fabrication and Modeling of Gigahertz Photodetectors in Heteroepitaxial Ge-on-Si Using a Graded Buffer Layer Deposited by Low Energy Plasma Enhanced CVD." IEDM p793 (2002)

EXAMINER Ashe Umman Sarhan	DATE CONSIDERED 1/30/06
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.